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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT		ATTY. DOCKET 033035 M 0342	SERIAL NO. 10/691,569
		APPLICANT: Kensaku MOTOKI, et al.	
		FILING DATE October 24, 2003	GROUP ART UNIT 2814

#### U.S. PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE, IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

#### FOREIGN PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION YES      NO
	AL						
	AM						
	AN						
	AO						
	AP						

#### OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>MM</i>	AQ	Nam et al. "Growth of GaN and Al <sub>10</sub> Ga <sub>0.8</sub> N on Patterned Substrates via Organometallic Vapor Phase Epitaxy" Jpn.j. Appl. Phys. Vol 36 (May 1, 1997), Pt. 2, No. 5A, pg. L532
	AR	
	AS	

EXAMINER:	DATE CONSIDERED:
<i>Maren D. Goss</i>	<i>2/19/2007</i>
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	